

Features

- Superior circuit protection
- Overcurrent and overvoltage protection
- Blocks surges up to rated limits
- High speed performance
- Small SMT package
- RoHS compliant*
- Agency recognition: 🔊

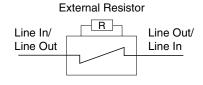
Applications

- Voice / VDSL cards
- Protection modules and dongles
- Process control equipment
- Test and measurement equipment
- General electronics

TBU-CX Series - TBU™ High Speed Protectors

General Information

The TBU-CX Series of Bourns® TBU™ products are low capacitance dual bidirectional high speed protection components, constructed using MOSFET semiconductor technology, and designed to protect against faults caused by short circuits, AC power cross, induction and lightning surges.



Agency Approval

Description							
UL	File Number: Pending						

The TBU™ high speed protector placed in the system circuit will monitor the current with the MOSFET detection circuit triggering to provide an effective barrier behind which sensitive electronics will not be exposed to large voltages or currents during surge events. The TBU™ device is provided in a surface mount DFN package and meets industry standard requirements such as RoHS and Pb Free solder reflow profiles.

Absolute Maximum Ratings (@ T_A = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Part Number	Value	Unit
		TBU-CX025-VTC-WH	250	
		TBU-CX040-VTC-WH	400	
V _{imp}	Peak impulse voltage withstand with duration less than 10 ms	TBU-CX050-VTC-WH	500	V
· ·		TBU-CX065-VTC-WH	650	
		TBU-CX085-VTC-WH	850	
		TBU-CX025-VTC-WH	100	
		TBU-CX040-VTC-WH	200	
V _{rms}	Continuous A.C. RMS voltage	TBU-CX050-VTC-WH	250	V
		TBU-CX065-VTC-WH	300	
		TBU-CX085-VTC-WH	425	
T _{op}	Operating temperature range	-40 to +125	°C	
T _{stg}	Storage temperature range	-65 to +150	°C	
T _{imax}	Maximum Junction Temperature	+125	°C	
ESD	HBM ESD Protection per IEC 61000-4-2	±2	kV	

Electrical Characteristics (@ T_A = 25 °C Unless Otherwise Noted)

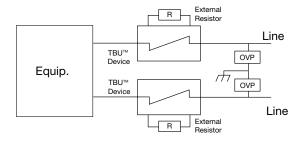
Symbol	Parameter		Part Number	Min.	Тур.	Max.	Unit
I _{trigger}	Current required for the protected state (Rexter	e device to go from operating state to r _{nal} = 0 ohm)	TBU-CXxxx-VTC-WH	500	750	1000	mA
R _{TBU}	Series resistance of the TBU device (R _{external} = 0 ohm)	$\begin{aligned} &V_{imp} = 250 \text{ V } &I_{trigger} \text{ (min.)} = 500 \text{ mA} \\ &V_{imp} = 400 \text{ V } &I_{trigger} \text{ (min.)} = 500 \text{ mA} \\ &V_{imp} = 500 \text{ V } &I_{trigger} \text{ (min.)} = 500 \text{ mA} \\ &V_{imp} = 650 \text{ V } &I_{trigger} \text{ (min.)} = 500 \text{ mA} \\ &V_{imp} = 850 \text{ V } &I_{trigger} \text{ (min.)} = 500 \text{ mA} \end{aligned}$	TBU-CX025-VTC-WH TBU-CX040-VTC-WH TBU-CX050-VTC-WH TBU-CX065-VTC-WH TBU-CX085-VTC-WH		2.6 3.6 5.0 7.0 10.7	3.0 4.2 5.7 8.0 13.0	Ω
t _{block}	Time for the device to			1	μs		
IQ	Current through the tri	0.25	0.50	1.00	mA		
V _{reset}	Voltage below which the state	12	16	20	V		
R _{th(j-l)}	Junction to package p		98		°C/W		
R _{th(j-l)}	Junction to package p		40		°C/W		

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Reference Application

The TBU™ devices are general use protectors used in a wide variety of applications. The maximum voltage rating of the TBU device should never be exceeded. Where necessary, an OVP should be employed to limit the maximum voltage. A costeffective protection solution combines Bourns® TBU™ protection devices with a pair of Bourns® MOVs. For bandwidth sensitive applications, a Bourns® GDT may be substituted for the MOV. See "Trigger Current vs External Resistor Value" graph for selecting the optimum trigger current value using a 0 ohm − 50 ohm resistor value.

Note: Line Resistance = TBU^{TM} Device Resistance + $R_{external}$ Resistance



Basic TBU Operation

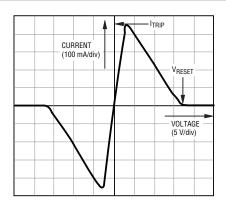
The TBU™ device, constructed using MOSFET semiconductor technology, placed in the system circuit will monitor the current with the MOSFET detection circuit triggering to provide an effective barrier behind which sensitive electronics are not exposed to large voltages or currents during surge events. The TBU™ device operates in approximately 1 µs - once line current exceeds the TBU™ device's trigger current Itrigger. When operated, the TBU™ device restricts line current to less than 1 mA typically. When operated, the TBU™ device will block all voltages including the surge up to rated limits.

After the surge, the TBUTM device resets when the voltage across the TBUTM device falls to the V_{reset} level. The TBUTM device will automatically reset on lines which have no DC bias or have DC bias below V_{reset} (such as unpowered signal lines).

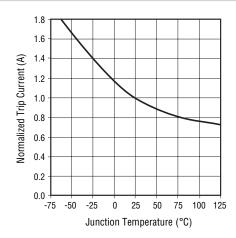
If the line has a normal DC bias above V_{reset} , the voltage across the TBUTM device may not fall below V_{reset} after the surge. In such cases, special care needs to be taken to ensure that the TBUTM device will reset, with software monitoring as one method used to accomplish this. Bourns application engineers can provide further assistance.

Performance Graphs

Typical V-I Characteristics (TBU-CX050-VTC-WH with Rext = 1 Ω)



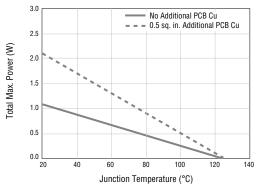
Typical Trigger Current vs. Temperature



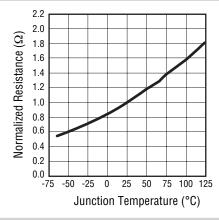
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Performance Graphs (Continued)

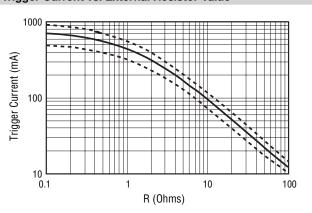
Power Derating Curve



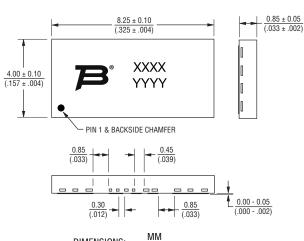
Typical Resistance vs. Temperature



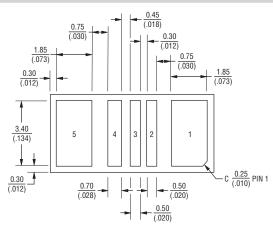
Trigger Current vs. External Resistor Value



Product Dimensions



DIMENSIONS: MIM (INCHES)



Pad Designation

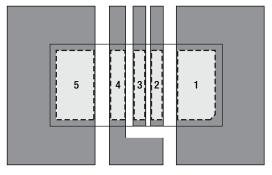
Pad #	Pin Out						
1	Line In/Out						
2	External R Pad						
3	External R Pad						
4	NU						
5	Line Out/In						

Specifications are subject to change without notice. Customers should verify actual device performance in their specific applications.

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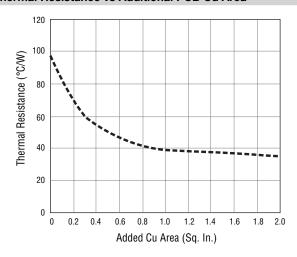
Recommended Pad Layout

TBU™ protectors have matte-tin termination finish. The suggested layout should use Non-Solder Mask Define (NSMD). The recommended stencil thickness is 0.10-0.12 mm (.004-.005 in.) with a stencil opening size 0.025 mm (.0010 in.) less than the device pad size. As when heat sinking any power device, it is recommended that wherever possible, extra PCB copper area is allowed. For minimum parasitic capacitance, do not allow any signal, ground or power signals beneath any of the pads of the device.



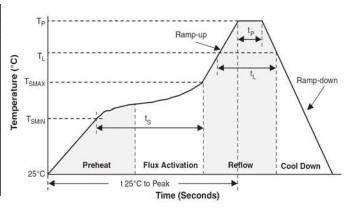
Dark grey areas show added PCB copper area for better thermal resistance.

Thermal Resistance vs Additional PCB Cu Area

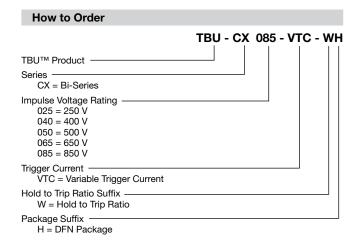


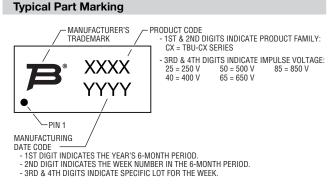
Reflow Profile

Profile Feature	Pb-Free Assembly
Average Ramp-Up Rate (Tsmax to Tp)	3 °C/sec. max.
Preheat - Temperature Min. (Tsmin) - Temperature Max. (Tsmax) - Time (tsmin to tsmax)	150 °C 200 °C 60-180 sec.
Time maintained above: - Temperature (TL) - Time (tL)	217 °C 60-150 sec.
Peak/Classification Temperature (Tp)	260 °C
Time within 5 °C of Actual Peak Temp. (tp)	20-40 sec.
Ramp-Down Rate	6 °C/sec. max.
Time 25 °C to Peak Temperature	8 min. max.



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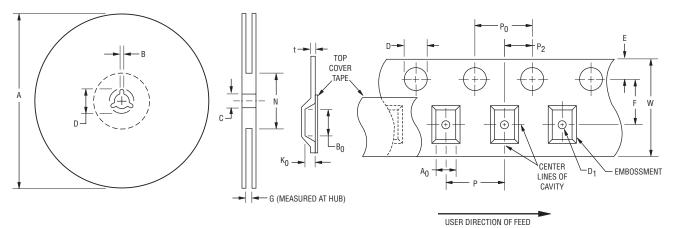




6-MONTH PERIOD CODES:

B = JUL-DEC 2009 D = JUL-DEC 2010 F = JUL-DEC 2011

Packaging Specifications



QUANTITY: 3000 PIECES PER REEL

	A	В		С		D		G	N
Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Ref.	Ref.
326	330	1.5	2.5	12.8	13.5	20.2		16.5	102
(12.835)	(13.002)	(.059)	(.098)	(.504)	(.531)	(.795)	_	(.650)	(4.016)

P	1 0	В	30	I))1	E		F	
Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	max.
4.3 (.169)	4.5 (.177)	8.45 (.333)	8.65 (.341)	1.5 (.059)	1.6 (.063)	1.5 (.059)	-	1.65 (.065)	1.85 (.073)	7.4 (.291)	7.6 (.299)
K	K ₀		P	P ₀		P ₂		t		W	
Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
1.0	1.2	7.9	8.1	3.9	4.1	1.9	2.1	0.25	0.35	15.7	16.3
(.039)	(.047)	(.311)	(.319)	(.159)	(.161)	(.075)	(.083)	(.010)	(.014)	(.618)	(.642)

DIMENSIONS: $\frac{MM}{(INCHES)}$